

## 620 µA, 2 MHz Auto-Zeroed Op Amps

#### **Features**

- · High DC Precision:
  - V<sub>OS</sub> Drift: ±50 nV/°C (maximum)
  - V<sub>OS</sub>: ±2 μV (maximum)
  - A<sub>OL</sub>: 125 dB (minimum)
  - PSRR: 125 dB (minimum)
  - CMRR: 120 dB (minimum)
  - $E_{ni}$ : 1.0  $\mu$ V<sub>P-P</sub> (typical), f = 0.1 Hz to 10 Hz
  - $E_{ni}$ : 0.32  $\mu V_{P-P}$  (typical), f = 0.01 Hz to 1 Hz
- · Low Power and Supply Voltages:
  - I<sub>O</sub>: 620 μA/amplifier (typical)
  - Wide Supply Voltage Range: 2.3V to 5.5V
- · Easy to Use:
  - Rail-to-Rail Input/Output
  - Gain Bandwidth Product: 2 MHz (typical)
  - Unity Gain Stable
  - Available in Dual
- Extended Temperature Range: -40°C to +125°C

#### **Typical Applications**

- · Portable Instrumentation
- · Sensor Conditioning
- · Temperature Measurement
- DC Offset Correction
- · Medical Instrumentation

#### **Design Aids**

- · SPICE Macro Models
- FilterLab<sup>®</sup> Software
- Microchip Advanced Part Selector (MAPS)
- · Analog Demonstration and Evaluation Boards
- Application Notes

#### **Related Parts**

Parts with lower power, lower bandwidth and higher noise:

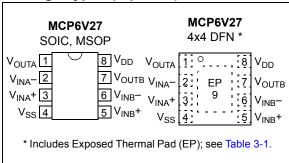
- MCP6V01/2/3: Spread clock
- MCP6V06/7/8: Non-spread clock

#### **Description**

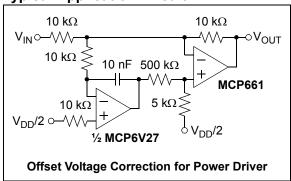
The Microchip Technology Inc. MCP6V27 dual operational amplifier has input offset voltage correction for very low offset and offset drift. This device has a wide gain bandwidth product (2 MHz, typical) and strongly rejects switching noise. It is unity gain stable, has no 1/f noise, and has good PSRR and CMRR. This product operates with a single supply voltage as low as 2.3V, while drawing 620  $\mu$ A/amplifier (typical) of quiescent current.

The Microchip Technology Inc. MCP6V27 op amp is offered as a dual. It is designed in an advanced CMOS process.

#### Package Types (top view)



#### Typical Application Circuit



NOTES:

# 1.0 ELECTRICAL CHARACTERISTICS

### 1.1 Absolute Maximum Ratings †

V <sub>DD</sub> – V <sub>SS</sub>	6.5V
Current at Input Pins ††	±2 mA
Analog Inputs (V <sub>IN</sub> + and V <sub>IN</sub> -) †† V <sub>SS</sub>	$_{\rm S}$ – 1.0V to V <sub>DD</sub> +1.0V
All other Inputs and OutputsV <sub>SS</sub>	$_{\rm S}$ – 0.3V to V <sub>DD</sub> +0.3V
Difference Input voltage	V <sub>DD</sub> – V <sub>SS</sub>
Output Short Circuit Current	Continuous
Current at Output and Supply Pins	±30 mA
Storage Temperature	65°C to +150°C
Max. Junction Temperature	+150°C
ESD protection on all pins (HBM, CDM, MM)	$\geq$ 4 kV,1.5 kV, 300V

† Notice: Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at those or any other conditions above those indicated in the operational listings of this specification is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability.

†† See Section 4.2.1, Rail-to-Rail Inputs.

### 1.2 Specifications

TABLE 1-1: DC ELECTRICAL SPECIFICATIONS

Parameters		Min		Max	Units	re 1-5).  Conditions
Parameters	Sym	IVIIII	Тур	IVIAX	Units	Conditions
Input Offset						
Input Offset Voltage	V <sub>OS</sub>	-2	_	+2	μV	$T_A = +25^{\circ}C$ (Note 1)
Input Offset Voltage Drift with Temperature (linear Temp. Co.)	TC <sub>1</sub>	-50	_	+50	nV/°C	T <sub>A</sub> = -40 to +125°C (Note 1)
nput Offset Voltage Quadratic Temperature Coefficient	TC <sub>2</sub>	_	±0.2	_	nV/°C <sup>2</sup>	$T_A = -40 \text{ to } +125^{\circ}\text{C}$
Power Supply Rejection	PSRR	125	142	_	dB	(Note 1)
Input Bias Current and Impedance						
Input Bias Current	Ι <sub>Β</sub>	_	+7	_	pА	
Input Bias Current across Temperature	I <sub>B</sub>	_	+110	_	pA	T <sub>A</sub> = +85°C
	I <sub>B</sub>	_	+1.2	+5	nA	T <sub>A</sub> = +125°C
nput Offset Current	Ios	_	±70	_	pА	
nput Offset Current across Temperature	I <sub>OS</sub>	_	±50	_	pA	T <sub>A</sub> = +85°C
	Ios	_	±60	_	pА	T <sub>A</sub> = +125°C
Common Mode Input Impedance	Z <sub>CM</sub>	_	10 <sup>13</sup>   12	_	$\Omega    pF$	
Differential Input Impedance	Z <sub>DIFF</sub>	_	10 <sup>13</sup>   12	_	Ω  pF	

Note 1: Set by design and characterization. Due to thermal junction and other effects in the production environment, these parts can only be screened in production (except TC<sub>1</sub>; see Appendix B: "Offset Related Test Screens").

<sup>2:</sup> Figure 2-18 shows how V<sub>CML</sub> and V<sub>CMH</sub> changed across temperature for the first production lot.

TABLE 1-1: DC ELECTRICAL SPECIFICATIONS (CONTINUED)

**Electrical Characteristics:** Unless otherwise indicated,  $T_A = +25^{\circ}C$ ,  $V_{DD} = +2.3V$  to +5.5V,  $V_{SS} = GND$ ,  $V_{CM} = V_{DD}/3$ ,  $V_{OUT} = V_{DD}/2$ ,  $V_L = V_{DD}/2$  and  $R_L = 10 \text{ k}\Omega$  to  $V_L$  (refer to Figure 1-4 and Figure 1-5). Max Units **Conditions Parameters** Sym Min Typ Common Mode  $V_{SS} - 0.15$ ٧ Common-Mode Input  $V_{CML}$ (Note 2) Voltage Range Low Common-Mode Input  $V_{\text{CMH}}$  $V_{DD} + 0.2$ ٧ (Note 2) Voltage Range High dΒ Common-Mode Rejection CMRR 120  $V_{DD} = 2.3V$ , 136  $V_{CM} = -0.15V \text{ to } 2.5V$ (Note 1, Note 2) CMRR 125 142 dB  $V_{DD} = 5.5V$ ,  $V_{CM} = -0.15V \text{ to } 5.7V$ (Note 1, Note 2) **Open-Loop Gain** DC Open-Loop Gain (large signal) dB  $V_{DD} = 2.3V$ , 125 147  $A_{OL}$  $V_{OUT} = 0.2V \text{ to } 2.1V$ (Note 1)  $\mathsf{A}_\mathsf{OL}$  $V_{DD} = 5.5V$ , 133 155 dB  $V_{OUT} = 0.2V \text{ to } 5.3V$ (Note 1) Output  $V_{OL}$ Minimum Output Voltage Swing G = +2, 0.5V $V_{SS} + 5$  $V_{SS} + 15$ mV input overdrive V<sub>DD</sub> – 15 G = +2.0.5VMaximum Output Voltage Swing  $V_{OH}$  $V_{DD} - 5$ mV input overdrive  $V_{DD} = 2.3V$ **Output Short Circuit Current**  $I_{SC}$ ±12 mΑ  $I_{SC}$ ±22 mΑ  $V_{DD} = 5.5V$ **Power Supply** Supply Voltage  $V_{DD}$ 2.3 5.5 ٧ Quiescent Current per amplifier 450 800  $I_Q$ 620 μΑ  $I_0 = 0$ 

1.15

 $V_{POR}$ 

1.65

POR Trip Voltage

Note 1: Set by design and characterization. Due to thermal junction and other effects in the production environment, these parts can only be screened in production (except TC<sub>1</sub>; see Appendix B: "Offset Related Test Screens").

<sup>2:</sup> Figure 2-18 shows how V<sub>CML</sub> and V<sub>CMH</sub> changed across temperature for the first production lot.

TABLE 1-2: AC ELECTRICAL SPECIFICATIONS

**Electrical Characteristics:** Unless otherwise indicated,  $T_A = +25$ °C,  $V_{DD} = +2.3$ V to +5.5V,  $V_{SS} = GND$ ,  $V_{CM} = V_{DD}/3$ ,  $V_{OUT} = V_{DD}/2$ ,  $V_L = V_{DD}/2$ ,  $R_L = 10 \text{ k}\Omega$  to  $V_L$  and  $C_L = 60 \text{ pF}$  (refer to Figure 1-4 and Figure 1-5). Min **Parameters** Sym Тур Max Units **Conditions Amplifier AC Response** Gain Bandwidth Product **GBWP** 2.0 MHz Slew Rate SR 1.0 V/µs Phase Margin PM 65 G = +1**Amplifier Noise Response** Input Noise Voltage  $E_{ni}$ 0.32 f = 0.01 Hz to 1 Hz $\mu V_{P-P}$  $E_{ni}$ 1.0  $\mu V_{P-P}$ f = 0.1 Hz to 10 Hz f < 5 kHzInput Noise Voltage Density e<sub>ni</sub> 50 nV/√Hz 29 nV/√Hz f = 100 kHz  $e_{ni}$ Input Noise Current Density fA/√Hz 0.6 i<sub>ni</sub> **Amplifier Distortion (Note 1)** Intermodulation Distortion (AC) IMD 40  $\mu V_{PK}$  $V_{CM}$  tone = 50 m $V_{PK}$  at 1 kHz,  $G_N = 1$ **Amplifier Step Response** Start Up Time 75 μs G = +1,  $V_{OS}$  within 50  $\mu V$  of its final value  $t_{STR}$ (Note 2) G = +1,  $V_{IN}$  step of 2V, 150 Offset Correction Settling Time t<sub>STL</sub> μs V<sub>OS</sub> within 50 μV of its final value G = -100,  $\pm 0.5V$  input overdrive to  $V_{DD}/2$ , Output Overdrive Recovery Time 45 μs todr V<sub>IN</sub> 50% point to V<sub>OUT</sub> 90% point (Note 3)

- **Note 1:** These parameters were characterized using the circuit in Figure 1-6. In Figure 2-37 and Figure 2-38, there is an IMD tone at DC, a residual tone at 1 kHz, other IMD tones and clock tones.
  - 2: High gains behave differently; see Section 4.3.3, Offset at Power Up.
  - 3: t<sub>ODR</sub> includes some uncertainty due to clock edge timing.

#### TABLE 1-3: TEMPERATURE SPECIFICATIONS

<b>Electrical Characteristics:</b> Unless otherwise indicated, all limits are specified for: V <sub>DD</sub> = +2.3V to +5.5V, V <sub>SS</sub> = GND.							
Parameters	Sym	Min	Тур	Max	Units	Conditions	
Temperature Ranges							
Specified Temperature Range	T <sub>A</sub>	-40	_	+125	°C		
Operating Temperature Range	T <sub>A</sub>	-40	_	+125	°C	(Note 1)	
Storage Temperature Range	T <sub>A</sub>	-65	_	+150	°C		
Thermal Package Resistances							
Thermal Resistance, 8L-4x4 DFN	$\theta_{JA}$	_	48	_	°C/W	(Note 2)	
Thermal Resistance, 8L-MSOP	$\theta_{JA}$	_	211	_	°C/W		
Thermal Resistance, 8L-SOIC	$\theta_{JA}$	_	150	_	°C/W		

- **Note 1:** Operation must not cause T<sub>J</sub> to exceed Maximum Junction Temperature specification (+150°C).
  - 2: Measured on a standard JC51-7, four layer printed circuit board with ground plane and vias.

#### 1.3 Timing Diagrams

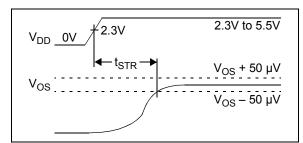
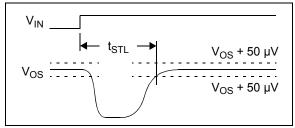


FIGURE 1-1: Amplifier Start Up.



**FIGURE 1-2:** Offset Correction Settling Time.

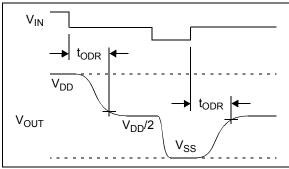


FIGURE 1-3: Output Overdrive Recovery.

#### 1.4 Test Circuits

The circuits used for the DC and AC tests are shown in Figure 1-4 and Figure 1-5. Lay the bypass capacitors out as discussed in **Section 4.3.10**, **Supply Bypassing and Filtering**.  $R_N$  is equal to the parallel combination of  $R_F$  and  $R_G$  to minimize bias current effects.

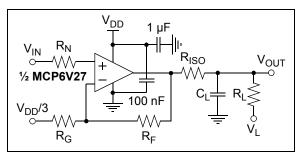


FIGURE 1-4: AC and DC Test Circuit for Most Non-Inverting Gain Conditions.

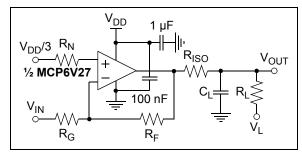


FIGURE 1-5: AC and DC Test Circuit for Most Inverting Gain Conditions.

The circuit in Figure 1-6 tests the op amp input's dynamic behavior (i.e., IMD,  $t_{STR}$ ,  $t_{STL}$  and  $t_{ODR}$ ). The potentiometer balances the resistor network ( $V_{OUT}$  should equal  $V_{REF}$  at DC). The op amp's common mode input voltage is  $V_{CM} = V_{IN}/2$ . The error at the input ( $V_{ERR}$ ) appears at  $V_{OUT}$  with a noise gain of 10 V/V.

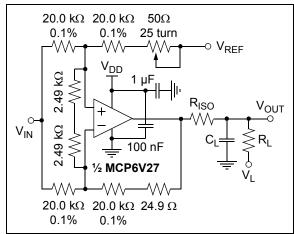


FIGURE 1-6: Test Circuit for Dynamic Input Behavior.

#### 2.0 TYPICAL PERFORMANCE CURVES

**Note:** The graphs and tables provided following this note are a statistical summary based on a limited number of samples and are provided for informational purposes only. The performance characteristics listed herein are not tested or guaranteed. In some graphs or tables, the data presented may be outside the specified operating range (e.g., outside specified power supply range) and therefore outside the warranted range.

**Note:** Unless otherwise indicated,  $T_A$  = +25°C,  $V_{DD}$  = +2.3V to 5.5V,  $V_{SS}$  = GND,  $V_{CM}$  =  $V_{DD}/3$ ,  $V_{OUT}$  =  $V_{DD}/2$ ,  $V_L$  =  $V_{DD}/2$ ,  $R_L$  = 10 k $\Omega$  to  $V_L$  and  $C_L$  = 60 pF.

#### 2.1 DC Input Precision

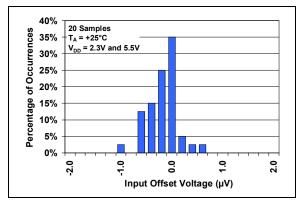


FIGURE 2-1: Input Offset Voltage.

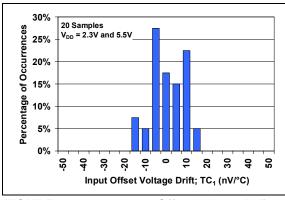
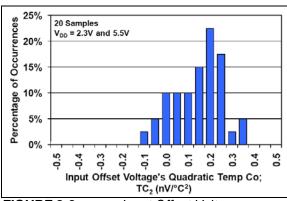
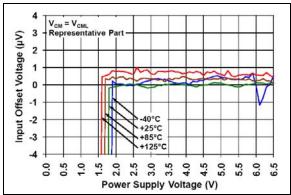


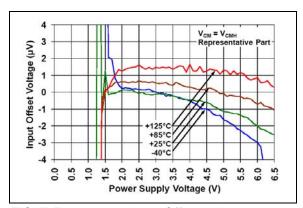
FIGURE 2-2: Input Offset Voltage Drift.



**FIGURE 2-3:** Input Offset Voltage Quadratic Temperature Coefficient.



**FIGURE 2-4:** Input Offset Voltage vs. Power Supply Voltage with  $V_{CM} = V_{CML}$ .



**FIGURE 2-5:** Input Offset Voltage vs. Power Supply Voltage with  $V_{CM} = V_{CMH}$ .

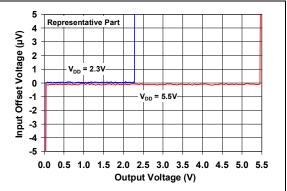
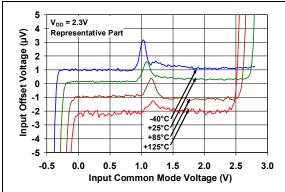
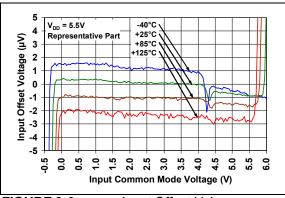


FIGURE 2-6: Input Offset Voltage vs. Output Voltage.

**Note:** Unless otherwise indicated,  $T_A$  = +25°C,  $V_{DD}$  = +2.3V to 5.5V,  $V_{SS}$  = GND,  $V_{CM}$  =  $V_{DD}/3$ ,  $V_{OUT}$  =  $V_{DD}/2$ ,  $V_L$  =  $V_{DD}/2$ ,  $R_L$  = 10 k $\Omega$  to  $V_L$  and  $C_L$  = 60 pF.



**FIGURE 2-7:** Input Offset Voltage vs. Common Mode Voltage with  $V_{DD} = 2.3V$ .



**FIGURE 2-8:** Input Offset Voltage vs. Common Mode Voltage with  $V_{DD} = 5.5V$ .

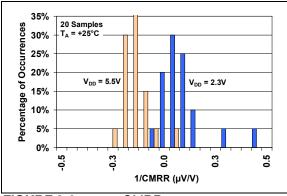


FIGURE 2-9: CMRR.

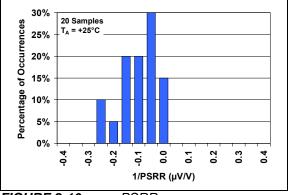


FIGURE 2-10: PSRR.

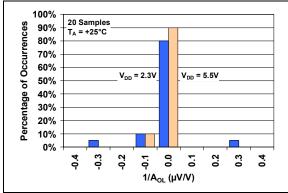
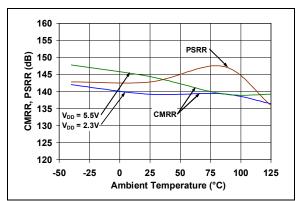
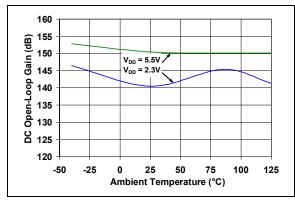


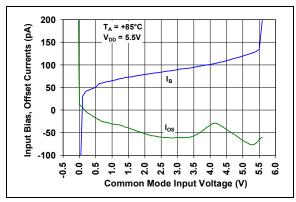
FIGURE 2-11: DC Open-Loop Gain.



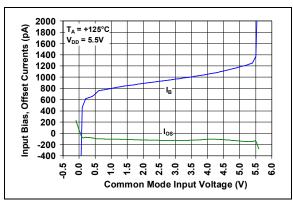
**FIGURE 2-12:** CMRR and PSRR vs. Ambient Temperature.



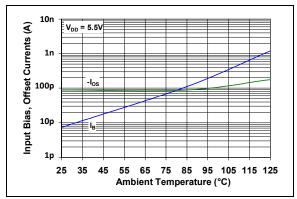
**FIGURE 2-13:** DC Open-Loop Gain vs. Ambient Temperature.



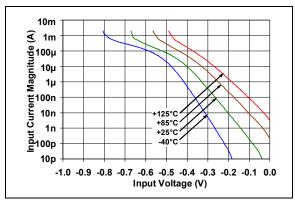
**FIGURE 2-14:** Input Bias and Offset Currents vs. Common Mode Input Voltage with  $T_A = +85$ °C.



**FIGURE 2-15:** Input Bias and Offset Currents vs. Common Mode Input Voltage with  $T_A = +125$ °C.



**FIGURE 2-16:** Input Bias and Offset Currents vs. Ambient Temperature with  $V_{DD} = +5.5V$ .



**FIGURE 2-17:** Input Bias Current vs. Input Voltage (below  $V_{SS}$ ).

## 2.2 Other DC Voltages and Currents

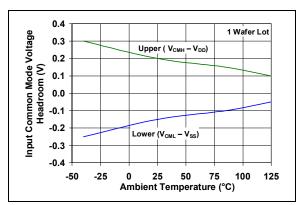


FIGURE 2-18: Input Common Mode Voltage Headroom (Range) vs. Ambient Temperature.

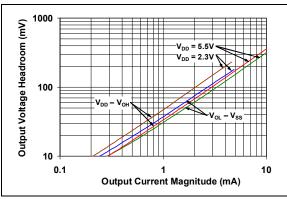
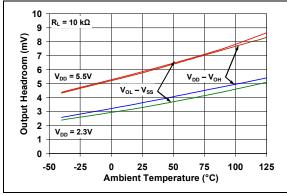
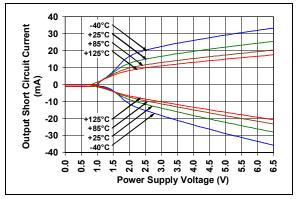


FIGURE 2-19: Output Voltage Headroom vs. Output Current.



**FIGURE 2-20:** Output Voltage Headroom vs. Ambient Temperature.



**FIGURE 2-21:** Output Short Circuit Current vs. Power Supply Voltage.

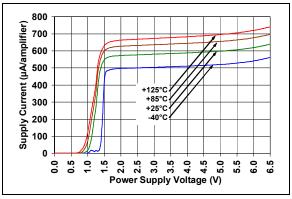


FIGURE 2-22: Supply Current vs. Power Supply Voltage.

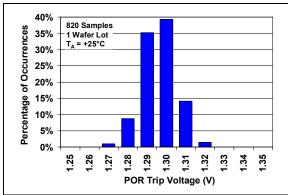
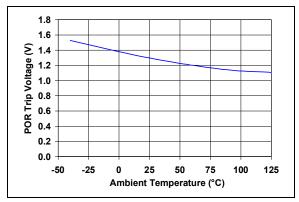


FIGURE 2-23: Power On Reset Trip Voltage.



**FIGURE 2-24:** Power On Reset Voltage vs. Ambient Temperature.

## 2.3 Frequency Response

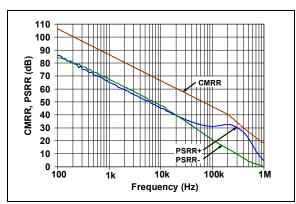


FIGURE 2-25: Frequency.

CMRR and PSRR vs.

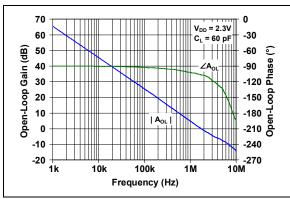
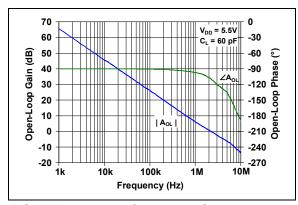


FIGURE 2-26: Open-Loop Gain vs. Frequency with  $V_{DD} = 2.3V$ .



**FIGURE 2-27:** Open-Loop Gain vs. Frequency with  $V_{DD} = 5.5V$ .

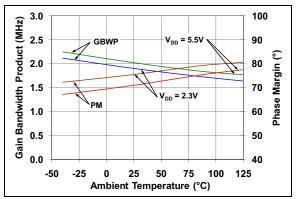
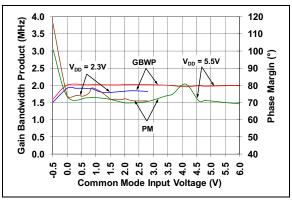
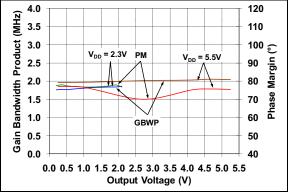


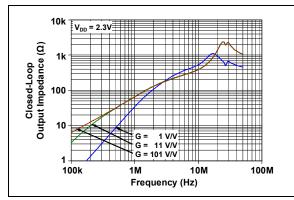
FIGURE 2-28: Gain Bandwidth Product and Phase Margin vs. Ambient Temperature.



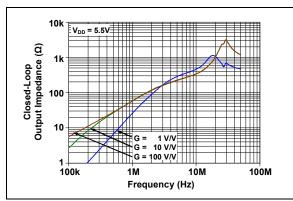
**FIGURE 2-29:** Gain Bandwidth Product and Phase Margin vs. Common Mode Input Voltage.



**FIGURE 2-30:** Gain Bandwidth Product and Phase Margin vs. Output Voltage.



**FIGURE 2-31:** Closed-Loop Output Impedance vs. Frequency with  $V_{DD} = 2.3V$ .



**FIGURE 2-32:** Closed-Loop Output Impedance vs. Frequency with  $V_{DD} = 5.5V$ .

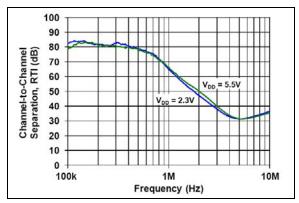
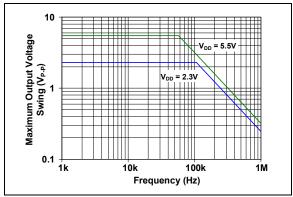
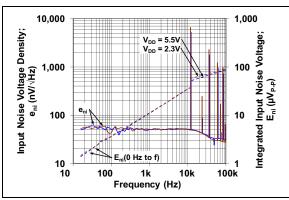


FIGURE 2-33: Channel-to-Channel Separation vs. Frequency.



**FIGURE 2-34:** Maximum Output Voltage Swing vs. Frequency.

### 2.4 Input Noise and Distortion



**FIGURE 2-35:** Input Noise Voltage Density and Integrated Input Noise Voltage vs. Frequency.

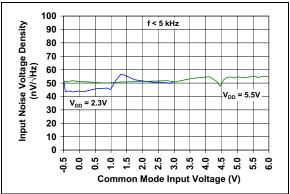
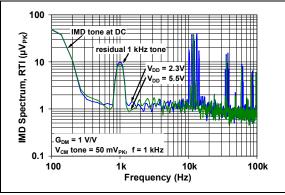
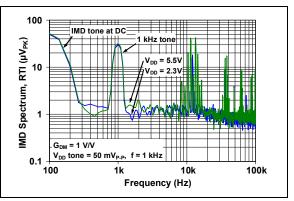


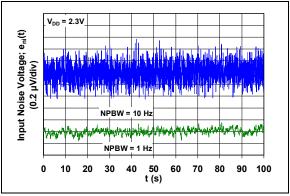
FIGURE 2-36: Input Noise Voltage Density vs. Input Common Mode Voltage.



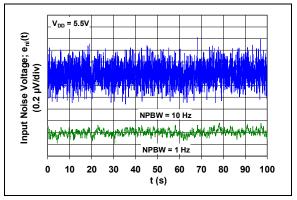
**FIGURE 2-37:** Inter-Modulation Distortion vs. Frequency with V<sub>CM</sub> Disturbance (see Figure 1-6).



**FIGURE 2-38:** Inter-Modulation Distortion vs. Frequency with  $V_{DD}$  Disturbance (see Figure 1-6).

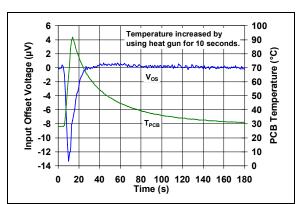


**FIGURE 2-39:** Input Noise vs. Time with 1 Hz and 10 Hz Filters and  $V_{DD} = 2.3V$ .

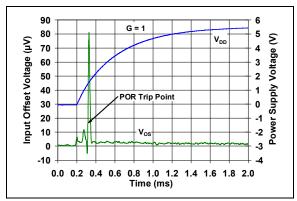


**FIGURE 2-40:** Input Noise vs. Time with 1 Hz and 10 Hz Filters and  $V_{DD} = 5.5V$ .

## 2.5 Time Response



**FIGURE 2-41:** Input Offset Voltage vs. Time with Temperature Change.



**FIGURE 2-42:** Input Offset Voltage vs. Time at Power Up.

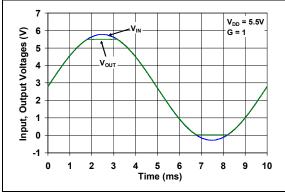


FIGURE 2-43: The MCP6V27 Device Shows No Input Phase Reversal with Overdrive.

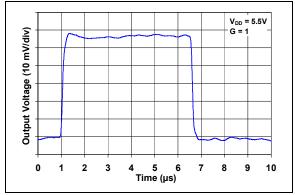


FIGURE 2-44: Non-inverting Small Signal Step Response.

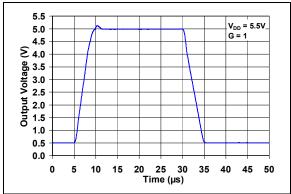


FIGURE 2-45: Non-inverting Large Signal Step Response.

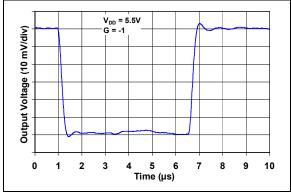
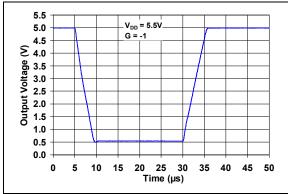


FIGURE 2-46: Inverting Small Signal Step Response.

**Note:** Unless otherwise indicated,  $T_A$  = +25°C,  $V_{DD}$  = +2.3V to 5.5V,  $V_{SS}$  = GND,  $V_{CM}$  =  $V_{DD}/3$ ,  $V_{OUT}$  =  $V_{DD}/2$ ,  $V_L$  =  $V_{DD}/2$ ,  $R_L$  = 10 k $\Omega$  to  $V_L$  and  $C_L$  = 60 pF.



**FIGURE 2-47:** Inverting Large Signal Step Response.

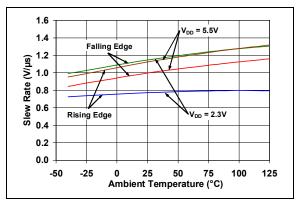
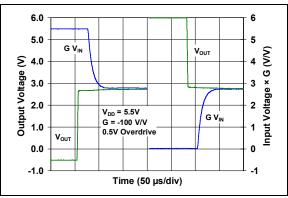
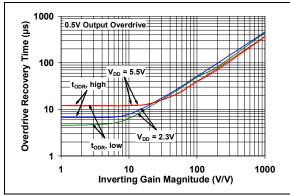


FIGURE 2-48: Temperature.

Slew Rate vs. Ambient



**FIGURE 2-49:** Output Overdrive Recovery vs. Time with G = -100 V/V.



**FIGURE 2-50:** Output Overdrive Recovery Time vs. Inverting Gain.

#### 3.0 PIN DESCRIPTIONS

Descriptions of the pins are listed in Table 3-1.

TABLE 3-1: PIN FUNCTION TABLE

МСР	P6V27	Symbol	Description
DFN	MSOP, SOIC	Symbol	Description
1	1	V <sub>OUT</sub> , V <sub>OUTA</sub>	Output (op amp A)
2	2	V <sub>IN</sub> -, V <sub>INA</sub> -	Inverting Input (op amp A)
3	3	$V_{IN}+$ , $V_{INA}+$	Non-inverting Input (op amp A)
4	4	$V_{SS}$	Negative Power Supply
5	5	V <sub>INB</sub> +	Non-inverting Input (op amp B)
6	6	V <sub>INB</sub> -	Inverting Input (op amp B)
7	7	V <sub>OUTB</sub>	Output (op amp B)
8	8	$V_{\mathrm{DD}}$	Positive Power Supply
9	_	EP	Exposed Thermal Pad (EP); must be connected to V <sub>SS</sub>

### 3.1 Analog Outputs

The analog output pins  $(V_{OUT})$  are low-impedance voltage sources.

#### 3.2 Analog Inputs

The non-inverting and inverting inputs  $(V_{IN}^+, V_{IN}^-, \ldots)$  are high-impedance CMOS inputs with low bias currents.

### 3.3 Power Supply Pins

The positive power supply ( $V_{DD}$ ) is 2.3V to 5.5V higher than the negative power supply ( $V_{SS}$ ). For normal operation, the other pins are between  $V_{SS}$  and  $V_{DD}$ .

Typically, these parts are used in a single (positive) supply configuration. In this case,  $V_{SS}$  is connected to ground and  $V_{DD}$  is connected to the supply.  $V_{DD}$  will need bypass capacitors.

### 3.4 Exposed Thermal Pad (EP)

There is an internal connection between the Exposed Thermal Pad (EP) and the  $V_{SS}$  pin; they must be connected to the same potential on the Printed Circuit Board (PCB).

This pad can be connected to a PCB ground plane to provide a larger heat sink. This improves the package thermal resistance ( $\theta_{JA}$ ).

NOTES:

#### 4.0 APPLICATIONS

The MCP6V27 auto-zeroed op amp is manufactured using Microchip's state of the art CMOS process. It is designed for low cost, low power and high precision applications. Its low supply voltage, low quiescent current and wide bandwidth makes the MCP6V27 device ideal for battery-powered applications.

# 4.1 Overview of Auto-Zeroing Operation

Figure 4-1 shows a simplified diagram of the MCP6V27 auto-zeroed op amp. This will be used to explain how the DC voltage errors are reduced in this architecture.

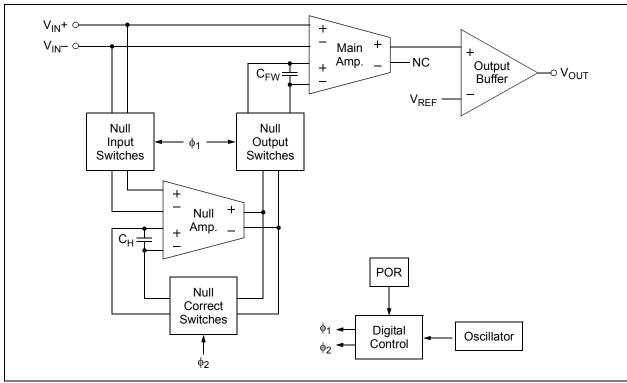


FIGURE 4-1: Simplified Auto-Zeroed Op Amp Functional Diagram.

#### 4.1.1 BUILDING BLOCKS

The Null Amplifier and Main Amplifier are designed for high gain and accuracy using a differential topology. They have a main input pair (+ and - pins at their top left) used for the signal. They have an auxiliary input pair (+ and - pins at their bottom left) used for correcting the offset voltages. Both input pairs are added together internally. The capacitors at the auxiliary inputs ( $C_{FW}$  and  $C_{H}$ ) hold the corrected values during normal operation.

The Output Buffer is designed to drive external loads at the  $V_{OUT}$  pin. It also produces a single ended output voltage ( $V_{RFF}$  is an internal reference voltage).

All of these switches are make-before-break in order to minimize glitch-induced errors. They are driven by two clock phases ( $\phi_1$  and  $\phi_2$ ) that select between normal mode and auto-zeroing mode.

The clock is derived from an internal R-C oscillator running at a rate of  $f_{OSC1}$  = 850 kHz. The oscillator's output is divided down to the desired rate.

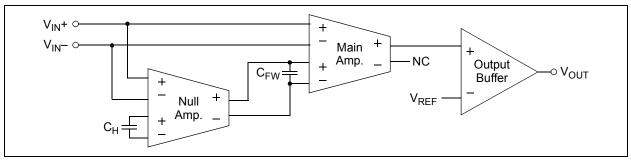
The internal POR ensures the part starts up in a known good state. It also provides protection against power supply brown-out events.

The Digital Control circuitry takes care of all of the housekeeping details of the switching operation. It also takes care of POR events.

#### 4.1.2 AUTO-ZEROING ACTION

Figure 4-2 shows the connections between amplifiers during the Normal Mode of operation  $(\phi_1)$ . The hold capacitor  $(C_H)$  corrects the Null Amplifier's input offset. Since the Null Amplifier has very high gain, it dominates the signal seen by the Main Amplifier. This greatly reduces the impact of the Main Amplifier's input

offset voltage on overall performance. Essentially, the Null Amplifier and Main Amplifier behave as a regular op amp with very high gain  $(A_{OL})$  and very low offset voltage  $(V_{OS})$ .

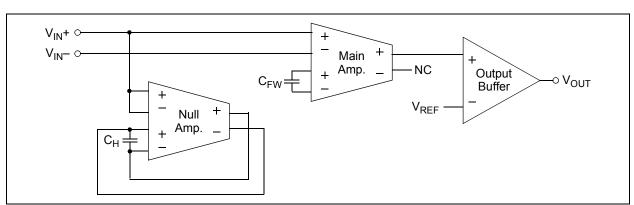


**FIGURE 4-2:** Normal Mode of Operation  $(\phi_1)$ ; Equivalent Amplifier Diagram.

Figure 4-3 shows the connections between amplifiers during the Auto-zeroing Mode of operation  $(\phi_2)$ . The signal goes directly through the Main Amplifier, and the flywheel capacitor  $(C_{FW})$  maintains a constant correction on the Main Amplifier's offset.

The Null Amplifier uses its own high open loop gain to drive the voltage across  $C_{\rm H}$  to the point where its input offset voltage is almost zero. Because the signal input pair is connected to  $V_{\rm IN}+$ , the auto-zeroing action corrects the offset at the current common mode input voltage ( $V_{\rm CM}$ ) and supply voltage ( $V_{\rm DD}$ ). This makes the DC CMRR and PSRR very high also.

Since these corrections happen every 40  $\mu$ s, or so, we also minimize slow errors, including offset drift with temperature ( $\Delta V_{OS}/\Delta T_A$ ), 1/f noise, and input offset aging.



**FIGURE 4-3:** Auto-zeroing Mode of Operation  $(\phi_2)$ ; Equivalent Diagram.

## 4.1.3 INTERMODULATION DISTORTION (IMD)

The MCP6V27 op amp will show intermodulation distortion (IMD), products when an AC signal is present.

The signal and clock can be decomposed into sine wave tones (Fourier series components). These tones interact with the auto-zeroing circuitry's non-linear response to produce IMD tones at sum and difference

frequencies. IMD distortion tones are generated about all of the square wave clock's harmonics. See Figure 2-37 and Figure 2-38.

#### 4.2 Other Functional Blocks

#### 4.2.1 RAIL-TO-RAIL INPUTS

The input stage of the MCP6V27 op amp uses two differential CMOS input stages in parallel. One operates at low common mode input voltage (V<sub>CM</sub>, which is approximately equal to V<sub>IN</sub>+ and V<sub>IN</sub>- in normal operation) and the other at high V<sub>CM</sub>. With this topology, the input operates with V<sub>CM</sub> up to V<sub>DD</sub> + 0.2V, and down to V<sub>SS</sub> – 0.15V, at +25°C (see Figure 2-18). The input offset voltage (V<sub>OS</sub>) is measured at V<sub>CM</sub> = V<sub>SS</sub> – 0.15V and V<sub>DD</sub> + 0.2V to ensure proper operation.

The transition between the input stages occurs when  $V_{CM} \approx V_{DD} - 1.2V$  (see Figure 2-7 and Figure 2-8). For the best distortion and gain linearity, with non-inverting gains, avoid this region of operation.

#### 4.2.1.1 Phase Reversal

The input devices are designed to not exhibit phase inversion when the input pins exceed the supply voltages. Figure 2-43 shows an input voltage exceeding both supplies with no phase inversion.

#### 4.2.1.2 Input Voltage Limits

In order to prevent damage and/or improper operation of these amplifiers, the circuit must limit the voltages at the input pins (see **Section 1.1, Absolute Maximum Ratings †**). This requirement is independent of the current limits discussed later on.

The ESD protection on the inputs can be depicted as shown in Figure 4-4. This structure was chosen to protect the input transistors against many (but not all) over-voltage conditions, and to minimize input bias current ( $I_B$ ).

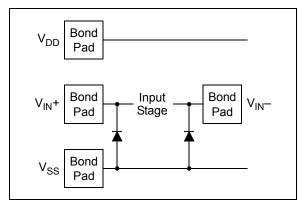
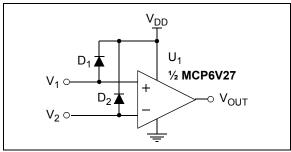


FIGURE 4-4: Simplified Analog Input ESD Structures.

The input ESD diodes clamp the inputs when they try to go more than one diode drop below  $V_{SS}$ . They also clamp any voltages that are well above  $V_{DD}$ ; their breakdown voltage is high enough to allow normal operation, but not low enough to protect against slow over-voltage (beyond  $V_{DD}$ ) events. Very fast ESD events (that meet the spec) are limited so that damage does not occur.

In some applications, it may be necessary to prevent excessive voltages from reaching the op amp inputs; Figure 4-5 shows one approach to protecting these inputs.  $D_1$  and  $D_2$  may be small signal silicon diodes, Schottky diodes for lower clamping voltages or diodeconnected FETs for low leakage.

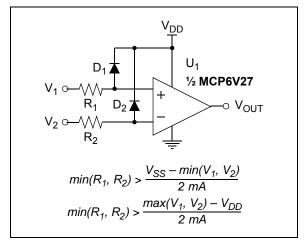


**FIGURE 4-5:** Protecting the Analog Inputs Against High Voltages.

#### 4.2.1.3 Input Current Limits

In order to prevent damage and/or improper operation of these amplifiers, the circuit must limit the currents into the input pins (see Section 1.1, Absolute Maximum Ratings †). This requirement is independent of the voltage limits previously discussed.

Figure 4-6 shows one approach to protecting these inputs. The resistors  $R_1$  and  $R_2$  limit the possible current in or out of the input pins (and into  $D_1$  and  $D_2$ ). The diode currents will dump onto  $V_{DD}$ .



**FIGURE 4-6:** Protecting the Analog Inputs Against High Currents.

It is also possible to connect the diodes to the left of resistors  $R_1$  and  $R_2.$  In this case, the currents through the diodes  $D_1$  and  $D_2$  need to be limited by some other mechanism. The resistors then serve as in-rush current limiters; the DC current into the input pins (V $_{\rm IN}+$  and V $_{\rm IN}-$ ) should be very small.

A significant amount of current can flow out of the inputs (through the ESD diodes) when the common mode voltage ( $V_{CM}$ ) is below ground ( $V_{SS}$ ); see Figure 2-17.

#### 4.2.2 RAIL-TO-RAIL OUTPUT

The output voltage range of the MCP6V27 zero-drift op amp is  $V_{DD}-15$  mV (minimum) and  $V_{SS}+15$  mV (maximum) when  $R_L=10$  k $\Omega$  is connected to  $V_{DD}/2$  and  $V_{DD}=5.5$ V. Refer to Figure 2-19 and Figure 2-20.

This op amp is designed to drive light loads; use another amplifier to buffer the output from heavy loads.

### 4.3 Application Tips

## 4.3.1 INPUT OFFSET VOLTAGE OVER TEMPERATURE

Table 1-1 gives both the linear and quadratic temperature coefficients (TC<sub>1</sub> and TC<sub>2</sub>) of input offset voltage. The input offset voltage, at any temperature in the specified range, can be calculated as follows:

#### **EQUATION 4-1:**

 $V_{OS}(T_A) = V_{OS} + TC_1\Delta T + TC_2\Delta T^2$  Where:  $\Delta T = T_A - 25^{\circ}C$   $V_{OS}(T_A) = \text{input offset voltage at } T_A$   $V_{OS} = \text{input offset voltage at } +25^{\circ}C$   $TC_1 = \text{linear temperature coefficient}$   $TC_2 = \text{quadratic temperature}$ 

#### 4.3.2 DC GAIN PLOTS

Figure 2-9, Figure 2-10 and Figure 2-11 are histograms of the reciprocals (in units of  $\mu\text{V/V})$  of CMRR, PSRR and  $A_{OL}$ , respectively. They represent the change in input offset voltage (V $_{OS}$ ) with a change in common mode input voltage (V $_{CM}$ ), power supply voltage (V $_{DD}$ ) and output voltage (V $_{OUT}$ ).

coefficient

The  $1/A_{OL}$  histogram is centered near 0  $\mu$ V/V because the measurements are dominated by the op amp's input noise. The negative values shown represent noise, *not* unstable behavior. We validate the op amps' stability by making multiple measurements of V<sub>OS</sub>; an unstable part would show either greater variability in V<sub>OS</sub>, or the output is stuck at one of the rails.

#### 4.3.3 OFFSET AT POWER UP

When this part powers up, the input offset ( $V_{OS}$ ) starts at its uncorrected value (usually less than  $\pm 5$  mV). Circuits with high DC gain can cause the output to reach one of the two rails. In this case, the time to a valid output is delayed by an output overdrive time (like  $t_{ODR}$ ), in addition to the startup time (like  $t_{STR}$ ).

It can be simple to avoid this extra startup time. Reducing the gain is one method. Adding a capacitor across the feedback resistor  $(R_{\text{F}})$  is another method.

#### 4.3.4 SOURCE RESISTANCES

The input bias currents have two significant components; switching glitches that dominate at room temperature and below, and input ESD diode leakage currents that dominate at +85°C and above.

Make the resistances seen by the inputs small and equal. This minimizes the output offset caused by the input bias currents.

The inputs should see a resistance on the order of  $10\Omega$  to  $1\,k\Omega$  at high frequencies (i.e., above 1 MHz). This helps minimize the impact of switching glitches, which are very fast, on overall performance. In some cases, it may be necessary to add resistors in series with the inputs to achieve this improvement in performance.

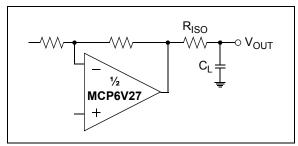
#### 4.3.5 SOURCE CAPACITANCE

The capacitances seen by the two inputs should be small and matched. The internal switches connected to the inputs dump charges on these capacitors; an offset can be created if the capacitances do not match.

#### 4.3.6 CAPACITIVE LOADS

Driving large capacitive loads can cause stability problems for voltage feedback op amps. As the load capacitance increases, the feedback loop's phase margin decreases and the closed-loop bandwidth is reduced. This produces gain peaking in the frequency response, with overshoot and ringing in the step response. These auto-zeroed op amps have a different output impedance than most op amps, due to their unique topology.

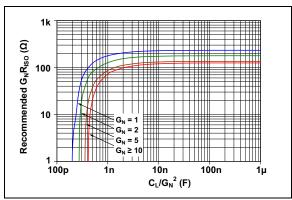
When driving a capacitive load with these op amps, a series resistor at the output ( $R_{\rm ISO}$  in Figure 4-7) improves the feedback loop's phase margin (stability) by making the output load resistive at higher frequencies. The bandwidth will be generally lower than the bandwidth with no capacitive load.



**FIGURE 4-7:** Output Resistor, R<sub>ISO</sub>, Stabilizes Capacitive Loads.

Figure 4-8 gives recommended  $R_{ISO}$  values for different capacitive loads and gains. The x-axis is the normalized load capacitance  $(C_L/G_N^2)$ . The y-axis is the normalized resistance  $(G_NR_{ISO})$ .

 $G_N$  is the circuit's noise gain. For non-inverting gains,  $G_N$  and the Signal Gain are equal. For inverting gains,  $G_N$  is 1+|Signal Gain| (e.g., -1 V/V gives  $G_N$  = +2 V/V).



**FIGURE 4-8:** Recommended R<sub>ISO</sub> values for Capacitive Loads.

After selecting  $R_{\rm ISO}$  for your circuit, double check the resulting frequency response peaking and step response overshoot. Modify  $R_{\rm ISO}$ 's value until the response is reasonable. Bench evaluation and simulations with the MCP6V27 SPICE macro model are helpful.

#### 4.3.7 STABILIZING OUTPUT LOADS

This auto-zeroed op amp has an output impedance (Figure 2-31 and Figure 2-32) that has a double zero when the gain is low. This can cause a large phase shift in feedback networks that have low resistance near the part's bandwidth. This large phase shift can cause stability problems.

Figure 4-9 shows that the load on the output is ( $R_L + R_{ISO}$ )||( $R_F + R_G$ ), where  $R_{ISO}$  is before the load (like Figures 4-7). This load needs to be large enough to maintain stability; it should be at least (2 k $\Omega$ )/ $G_N$ .

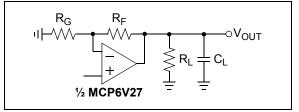


FIGURE 4-9:

Output Load.

#### 4.3.8 GAIN PEAKING

Figure 4-10 shows an op amp circuit that represents non-inverting amplifiers ( $V_M$  is a DC voltage and  $V_P$  is the input) or inverting amplifiers ( $V_P$  is a DC voltage and  $V_M$  is the input). The capacitances  $C_N$  and  $C_G$  represent the total capacitance at the input pins; they include the op amp's common mode input capacitance ( $C_{CM}$ ), board parasitic capacitance and any capacitor placed in parallel.

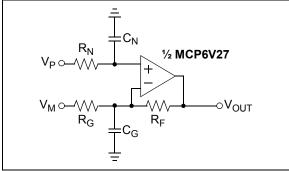


FIGURE 4-10: Amplifier with Parasitic Capacitance.

 $C_G$  acts in parallel with  $R_G$  (except for a gain of +1 V/V), which causes an increase in gain at high frequencies.  $C_G$  also reduces the phase margin of the feedback loop, which becomes less stable. This effect can be reduced by either reducing  $C_G$  or  $R_F || R_G$ .

 $C_N$  and  $R_N$  form a low-pass filter that affects the signal at  $V_P\!.$  This filter has a single real pole at  $1/(2\pi R_N C_N).$ 

The largest value of  $R_F$  that should be used depends on noise gain (see  $G_N$  in **Section 4.3.6**, **Capacitive Loads**),  $C_G$  and the open-loop gain's phase shift. An approximate limit for  $R_F$  is:

#### **EQUATION 4-2:**

$$R_F \leq 2 \; k\Omega \times \frac{12 \; pF}{C_G} \times G_N^2$$

Some applications may modify these values to reduce either output loading or gain peaking (step response overshoot).

## 4.3.9 REDUCING UNDESIRED NOISE AND SIGNALS

Reduce undesired noise and signals with:

- · Low bandwidth signal filters:
  - Minimizes random analog noise
  - Reduces interfering signals
- · Good PCB layout techniques:
  - Minimizes crosstalk
  - Minimizes parasitic capacitances and inductances that interact with fast switching edges
- · Good power supply design:
  - Provides isolation from other parts
  - Filters interference on supply line(s)

## 4.3.10 SUPPLY BYPASSING AND FILTERING

With this operational amplifier, the power supply pin ( $V_{DD}$  for single supply) should have a local bypass capacitor (i.e., 0.01  $\mu$ F to 0.1  $\mu$ F) within 2 mm of the pin for good high-frequency performance.

This part also needs a bulk capacitor (i.e.,  $1 \mu F$  or larger) within 100 mm to provide large, slow currents. This bulk capacitor can be shared with other low noise, analog parts.

In some cases, high-frequency power supply noise (e.g., switched mode power supplies) may cause undue intermodulation distortion, with a DC offset shift; this noise needs to be filtered. Adding a resistor into the supply connection can be helpful. This resistors needs to be small enough to prevent a large drop in  $V_{DD}$  for the op amp, which would cause a reduced output range and possible load-induced power supply noise. It also needs to be large enough to dissipate little power when  $V_{DD}$  is turned on and off quickly. Figure 4-11 shows a circuit with resistors in the supply connections. It gives good rejection out to 1 MHz for switched mode power supplies. Smaller resistors and capacitors are a better choice for designs where the power supply is not as noisy.

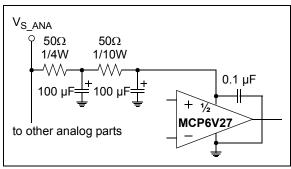


FIGURE 4-11: Additional Supply Filtering.

#### 4.3.11 PCB DESIGN FOR DC PRECISION

In order to achieve DC precision on the order of  $\pm 1~\mu V$ , many physical errors need to be minimized. The design of the Printed Circuit Board (PCB), the wiring and the thermal environment has a strong impact on the precision achieved. A poor PCB design can easily be more than 100 times worse than the MCP6V27 op amp minimum and maximum specifications.

#### 4.3.11.1 PCB Layout

Any time two dissimilar metals are joined together, a temperature dependent voltage appears across the junction (the Seebeck or thermo-junction effect). This effect is used in thermocouples to measure temperature. The following are examples of thermo-junctions on a PCB:

- Components (resistors, op amps, ...) soldered to a copper pad
- · Wires mechanically attached to the PCB
- · Jumpers
- · Solder joints
- PCB vias

Typical thermo-junctions have temperature to voltage conversion coefficients of 10 to 100  $\mu$ V/°C (sometimes higher).

Microchip's AN1258 ("Op Amp Precision Design: PCB Layout Techniques") contains in depth information on PCB layout techniques that minimize thermo-junction effects. It also discusses other effects, such as crosstalk, impedances, mechanical stresses and humidity.

#### 4.3.11.2 Crosstalk

DC crosstalk causes offsets that appear as a larger input offset voltage. Common causes include:

- · Common mode noise (remote sensors)
- · Ground loops (current return paths)
- · Power supply coupling

Interference from the mains (usually 50 Hz or 60 Hz), and other AC sources, can also affect the DC performance. Non-linear distortion can convert these signals to multiple tones, included a DC shift in voltage. When the signal is sampled by an ADC, these AC signals can also be aliased to DC, causing an apparent shift in offset

To reduce interference:

- Keep traces and wires as short as possible
- Use shielding (e.g., encapsulant)
- Use ground plane (at least a star ground)
- Place the input signal source near to the DUT
- Use good PCB layout techniques
- Use a separate power supply filter (bypass capacitors) for these auto-zeroed op amps

#### 4.3.11.3 Miscellaneous Effects

Keep the resistances seen by the input pins as small and as near to equal as possible to minimize bias current related offsets.

Make the (trace) capacitances seen by the input pins small and equal. This is helpful in minimizing switching glitch-induced offset voltages.

Bending a coax cable with a radius that is too small causes a small voltage drop to appear on the center conductor (the tribo-electric effect). Make sure the bending radius is large enough to keep the conductors and insulation in full contact.

Mechanical stresses can make some capacitor types (such as ceramic) to output small voltages. Use more appropriate capacitor types in the signal path and minimize mechanical stresses and vibration.

Humidity can cause electro-chemical potential voltages to appear in a circuit. Proper PCB cleaning helps, as does the use of encapsulants.

#### 4.4 Typical Applications

#### 4.4.1 WHEATSTONE BRIDGE

Many sensors are configured as Wheatstone bridges. Strain gauges and pressure sensors are two common examples. These signals can be small and the common mode noise large. Amplifier designs with high differential gain are desirable.

Figure 4-12 shows how to interface to a Wheatstone bridge with a minimum of components. Because the circuit is not symmetric, the ADC input is single ended, and there is a minimum of filtering, the CMRR is good enough for moderate common mode noise.

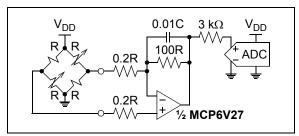


FIGURE 4-12: Simple Design.

Figure 4-13 shows a higher performance circuit for Wheatstone bridges. This circuit is symmetric and has high CMRR. Using a differential input to the ADC helps with the CMRR.

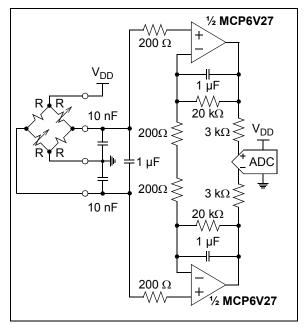


FIGURE 4-13: High Performance Design.

#### 4.4.2 RTD SENSOR

The ratiometric circuit in Figure 4-14 conditions a three wire RTD. It corrects for the sensor's wiring resistance by subtracting the voltage across the middle  $R_W$ . The top  $R_1$  does not change the output voltage; it balances the op amp inputs. Failure (open) of the RTD is detected by an out-of-range voltage.

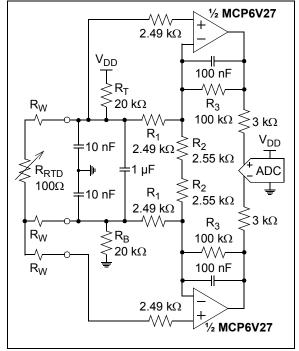


FIGURE 4-14: RTD Sensor.

The voltages at the input of the ADC can be calculated with the following:

$$G_{RTD} = 1 + 2 \cdot R_{3} / R_{2}$$

$$G_{W} = G_{RTD} - R_{3} / R_{1}$$

$$V_{DM} = G_{RTD}(V_{T} - V_{B}) + G_{W}V_{W}$$

$$V_{CM} = \frac{V_{T} + V_{B} + (G_{RTD} + 1 - G_{W})V_{W}}{2}$$

Where:

 $V_T$  = Voltage at the top of  $R_{RTD}$  $V_B$  = Voltage at the bottom of  $R_{RTD}$ 

 $V_W$  = Voltage across top and middle  $R_W$ 's

 $V_{CM}$  = ADC's common mode input  $V_{DM}$  = ADC's differential mode input

#### 4.4.3 THERMOCOUPLE SENSOR

Figure 4-15 shows a simplified diagram of an amplifier and temperature sensor used in a thermocouple application. The type K thermocouple senses the temperature at the hot junction ( $T_{HJ}$ ), and produces a voltage at  $V_1$  proportional to  $T_{HJ}$  (in °C). The amplifier's gain is set so that  $V_4/T_{HJ}$  is 10 mV/°C.  $V_3$  represents the output of a temperature sensor, which produces a voltage proportional to the temperature (in °C) at the cold junction ( $T_{CJ}$ ), and with a 0.50V offset.  $V_2$  is set so that  $V_4$  is 0.50V when  $T_{HJ}-T_{CJ}$  is 0°C.

#### **EQUATION 4-3:**

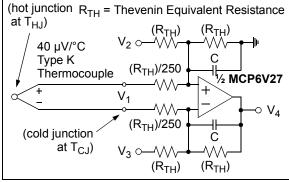
$$V_{1} \approx T_{HJ}(40 \,\mu\text{V/°C})$$

$$V_{2} = (1.00 \,\text{V})$$

$$V_{3} = T_{CJ}(10 \,\text{mV/°C}) + (0.50 \,\text{V})$$

$$V_{4} = 250 \,\text{V}_{1} + (\,\text{V}_{2} - \,\text{V}_{3})$$

$$\approx (10 \,\text{mV/°C}) \,(T_{HJ} - T_{CJ}) + (0.50 \,\text{V})$$



**FIGURE 4-15:** Thermocouple Sensor; Simplified Circuit.

Figure 4-16 shows a more complete implementation of this circuit. The dashed red arrow indicates a thermally conductive connection between the thermocouple and the MCP9700A; it needs to be very short and have low thermal resistance.

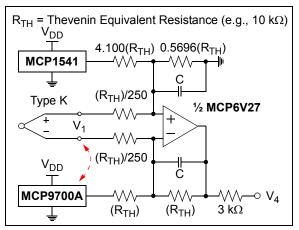


FIGURE 4-16: Thermocouple Sensor.

The MCP9700A senses the temperature at its physical location. It needs to be at the same temperature as the cold junction ( $T_{\rm CJ}$ ), and produces  $V_3$  (Figure 4-15).

The MCP1541 produces a 4.10V output, assuming  $V_{DD}$  is at 5.0V. This voltage, tied to a resistor ladder of 4.100( $R_{TH}$ ) and 1.3224( $R_{TH}$ ), would produce a Thevenin equivalent of 1.00V and 250( $R_{TH}$ ). The 1.3224( $R_{TH}$ ) resistor is combined in parallel with the top right  $R_{TH}$  resistor (in Figure 4-15), producing the 0.5696( $R_{TH}$ ) resistor.

V<sub>4</sub> should be converted to digital, then corrected for the thermocouple's non-linearity. The ADC can use the MCP1541 as its voltage reference. Alternately, an absolute reference inside a PICmicro<sup>®</sup> device can be used instead of the MCP1541.

#### 4.4.4 OFFSET VOLTAGE CORRECTION

Figure 4-17 shows an MCP6V27 correcting the input offset voltage of another op amp.  $R_2$  and  $C_2$  integrate the offset error seen at the other op amp's input; the integration needs to be slow enough to be stable (with the feedback provided by  $R_1$  and  $R_3$ ).

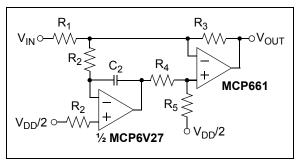


FIGURE 4-17: Offset Correction.

### 4.4.5 PRECISION COMPARATOR

Use high gain before a comparator to improve the latter's performance. Do not use MCP6V27 as a comparator by itself; the  $V_{OS}$  correction circuitry does not operate properly without a feedback loop.

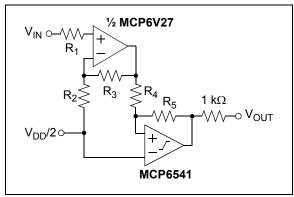


FIGURE 4-18: Precision Comparator.

NOTES:

#### 5.0 DESIGN AIDS

Microchip provides the basic design aids needed for the MCP6V27 op amp.

#### 5.1 SPICE Macro Model

The latest SPICE macro model for the MCP6V27 op amp is available on the Microchip web site at www.microchip.com. This model is intended to be an initial design tool that works well in the op amp's linear region of operation over the temperature range. See the model file for information on its capabilities.

Bench testing is a very important part of any design and cannot be replaced with simulations. Also, simulation results using this macro model need to be validated by comparing them to the data sheet specifications and characteristic curves.

### 5.2 FilterLab<sup>®</sup> Software

Microchip's FilterLab® software is an innovative software tool that simplifies analog active filter (using op amps) design. Available at no cost from the Microchip web site at <a href="https://www.microchip.com/filterlab">www.microchip.com/filterlab</a>, the Filter-Lab design tool provides full schematic diagrams of the filter circuit with component values. It also outputs the filter circuit in SPICE format, which can be used with the macro model to simulate actual filter performance.

# 5.3 Microchip Advanced Part Selector (MAPS)

MAPS is a software tool that helps efficiently identify Microchip devices that fit a particular design requirement. Available at no cost from the Microchip website at <a href="https://www.microchip.com/maps">www.microchip.com/maps</a>, the MAPS is an overall selection tool for Microchip's product portfolio that includes Analog, Memory, MCUs and DSCs. Using this tool, a customer can define a filter to sort features for a parametric search of devices and export side-by-side technical comparison reports. Helpful links are also provided for Data sheets, Purchase and Sampling of Microchip parts.

## 5.4 Analog Demonstration and Evaluation Boards

Microchip offers a broad spectrum of Analog Demonstration and Evaluation Boards that are designed to help customers achieve faster time to market. For a complete listing of these boards and their corresponding user's guides and technical information, visit the Microchip web site at <a href="https://www.microchip.com/analog">www.microchip.com/analog</a> tools.

Some boards that are especially useful are:

- MCP6V01 Thermocouple Auto-Zeroed Reference Design
- MCP6XXX Amplifier Evaluation Board 1
- MCP6XXX Amplifier Evaluation Board 2
- · MCP6XXX Amplifier Evaluation Board 3
- MCP6XXX Amplifier Evaluation Board 4
- · Active Filter Demo Board Kit
- P/N SOIC8EV: 8-Pin SOIC/MSOP/TSSOP/DIP Evaluation Board
- P/N SOIC14EV: 14-Pin SOIC/TSSOP/DIP Evaluation Board

#### 5.5 Application Notes

The following Microchip Application Notes are available on the Microchip web site at www.microchip. com/appnotes and are recommended as supplemental reference resources.

**ADN003:** "Select the Right Operational Amplifier for your Filtering Circuits", DS21821

**AN722:** "Operational Amplifier Topologies and DC Specifications", DS00722

**AN723:** "Operational Amplifier AC Specifications and Applications", DS00723

**AN884:** "Driving Capacitive Loads With Op Amps", DS00884

**AN990:** "Analog Sensor Conditioning Circuits – An Overview", DS00990

**AN1177:** "Op Amp Precision Design: DC Errors", DS01177

**AN1228:** "Op Amp Precision Design: Random Noise", DS01228

**AN1258:** "Op Amp Precision Design: PCB Layout Techniques". DS01258

These application notes and others are listed in the design guide:

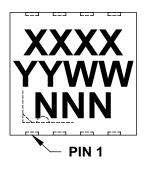
"Signal Chain Design Guide", DS21825

NOTES:

#### 6.0 PACKAGING INFORMATION

### 6.1 Package Marking Information

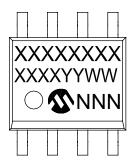
8-Lead DFN (4x4 mm)



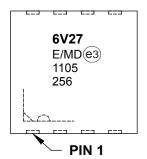
8-Lead MSOP



8-Lead SOIC (150 mil)



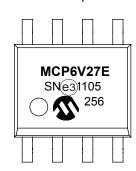
Example



Example



Example



Legend: XX...X Customer-specific information

Y Year code (last digit of calendar year)
YY Year code (last 2 digits of calendar year)
WW Week code (week of January 1 is week '01')
NNN Alphanumeric traceability code

e3 Pb-free JEDEC designator for Matte Tin (Sn)

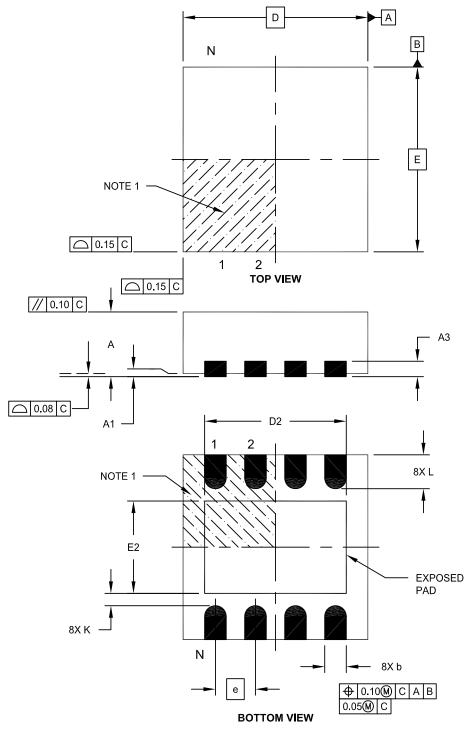
This package is Pb-free. The Pb-free JEDEC designator (e3)

can be found on the outer packaging for this package.

**Note**: In the event the full Microchip part number cannot be marked on one line, it will be carried over to the next line, thus limiting the number of available characters for customer-specific information.

## 8-Lead Plastic Dual Flat, No Lead Package (MD) – 4x4x0.9 mm Body [DFN]

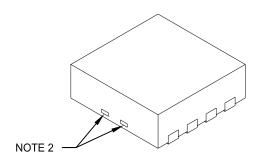
**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



Microchip Technology Drawing C04-131E Sheet 1 of 2

### 8-Lead Plastic Dual Flat, No Lead Package (MD) - 4x4x0.9 mm Body [DFN]

**ote:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



Units		MILLIMETERS		
Dimension	Dimension Limits		NOM	MAX
Number of Pins	N		8	
Pitch	е		0.80 BSC	
Overall Height	Α	0.80	0.90	1.00
Standoff	A1	0.00	0.02	0.05
Contact Thickness	A3	0.20 REF		
Overall Length	D		4.00 BSC	
Exposed Pad Width	E2	2.60	2.70	2.80
Overall Width	E		4.00 BSC	
Exposed Pad Length	D2	3.40	3.50	3.60
Contact Width	b	0.25	0.30	0.35
Contact Length	L	0.30	0.40	0.50
Contact-to-Exposed Pad	K	0.20	-	-

#### Notes:

- 1. Pin 1 visual index feature may vary, but must be located within the hatched area.
- 2. Package may have one or more exposed tie bars at ends.
- 3. Package is saw singulated
- 1. Dimensioning and tolerancing per ASME Y14.5M

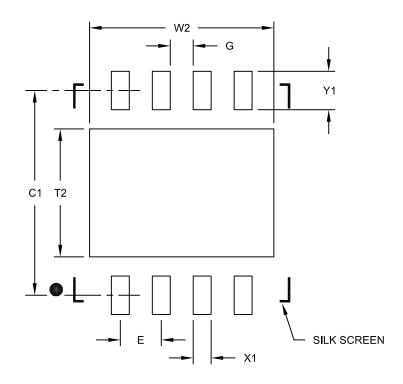
BSC: Basic Dimension. Theoretically exact value shown without tolerances.

REF: Reference Dimension, usually without tolerance, for information purposes only.

Microchip Technology Drawing C04-131E Sheet 2 of 2

## 8-Lead Plastic Dual Flat, No Lead Package (MD) - 4x4x0.9 mm Body [DFN]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



### RECOMMENDED LAND PATTERN

	I.	<b>IILLIMETER</b>	S	
Dimension Limits		MIN	NOM	MAX
Contact Pitch	E	0.80 BSC		
Optional Center Pad Width	W2			3.60
Optional Center Pad Length	T2			2.50
Contact Pad Spacing	C1		4.00	
Contact Pad Width (X8)	X1			0.35
Contact Pad Length (X8)	Y1			0.75
Distance Between Pads	G	0.45		

#### Notes:

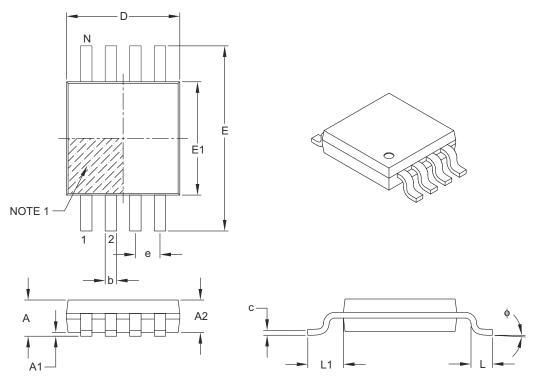
1. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing No. C04-2131C

### 8-Lead Plastic Micro Small Outline Package (MS) [MSOP]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



	Units	MILLIMETERS			
Dimens	ion Limits	MIN	NOM	MAX	
Number of Pins	N		8		
Pitch	е		0.65 BSC		
Overall Height	Α	_	_	1.10	
Molded Package Thickness	A2	0.75	0.85	0.95	
Standoff	A1	0.00	_	0.15	
Overall Width	Е	4.90 BSC			
Molded Package Width	E1		3.00 BSC		
Overall Length	D		3.00 BSC		
Foot Length	L	0.40	0.60	0.80	
Footprint	L1	0.95 REF			
Foot Angle	ф	0°	_	8°	
Lead Thickness	С	0.08	_	0.23	
Lead Width	b	0.22	_	0.40	

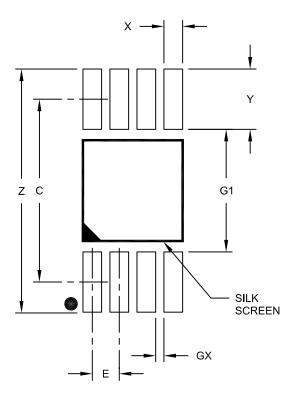
#### Notes:

- 1. Pin 1 visual index feature may vary, but must be located within the hatched area.
- 2. Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.15 mm per side.
- 3. Dimensioning and tolerancing per ASME Y14.5M.
  - BSC: Basic Dimension. Theoretically exact value shown without tolerances.
  - REF: Reference Dimension, usually without tolerance, for information purposes only.

Microchip Technology Drawing C04-111B

### 8-Lead Plastic Micro Small Outline Package (MS) [MSOP]

**lote:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



RECOMMENDED LAND PATTERN

	N	/ILLIMETER	S	
Dimension	Dimension Limits		NOM	MAX
Contact Pitch	Е		0.65 BSC	
Contact Pad Spacing	С		4.40	
Overall Width	Z			5.85
Contact Pad Width (X8)	X1			0.45
Contact Pad Length (X8)	Y1			1.45
Distance Between Pads	G1	2.95		·
Distance Between Pads	GX	0.20		

#### Notes

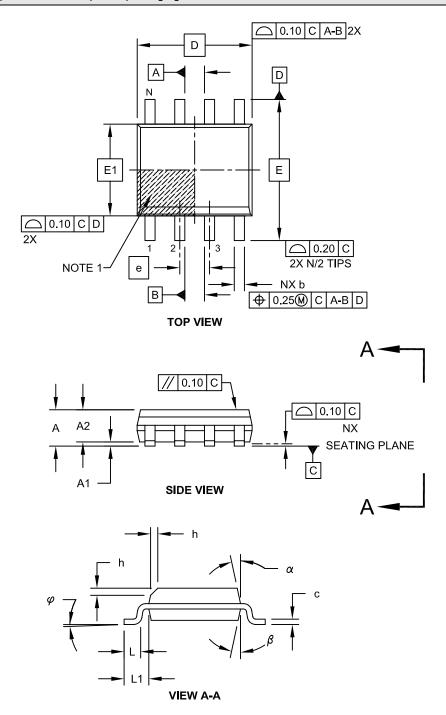
1. Dimensioning and tolerancing per ASME Y14.5M  $\,$ 

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing No. C04-2111A

## 8-Lead Plastic Small Outline (SN) - Narrow, 3.90 mm Body [SOIC]

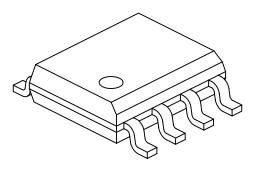
**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



Microchip Technology Drawing No. C04-057C Sheet 1 of 2

### 8-Lead Plastic Small Outline (SN) - Narrow, 3.90 mm Body [SOIC]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



	Units	N	1ILLIMETER	S
Dimension	Limits	MIN	NOM	MAX
Number of Pins	N		8	
Pitch	е		1.27 BSC	
Overall Height	Α	ı	ı	1.75
Molded Package Thickness	A2	1.25	ı	-
Standoff §	A1	0.10	ı	0.25
Overall Width	Е	6.00 BSC		
Molded Package Width	E1	3.90 BSC		
Overall Length	D		4.90 BSC	
Chamfer (Optional)	h	0.25	-	0.50
Foot Length	L	0.40	ı	1.27
Footprint	L1		1.04 REF	
Foot Angle	$\varphi$	0°	-	8°
Lead Thickness	С	0.17 - 0.25		
Lead Width	b	0.31	-	0.51
Mold Draft Angle Top	α	5°	-	15°
Mold Draft Angle Bottom	β	5°	-	15°

#### Notes:

- 1. Pin 1 visual index feature may vary, but must be located within the hatched area.
- 2. § Significant Characteristic
- 3. Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.15mm per side.
- 4. Dimensioning and tolerancing per ASME Y14.5M

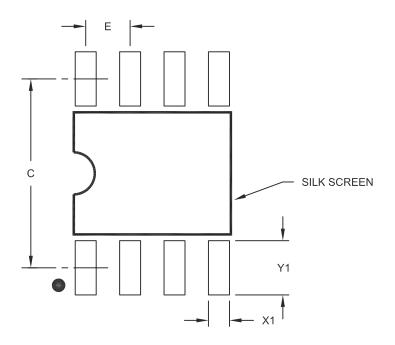
BSC: Basic Dimension. Theoretically exact value shown without tolerances.

 $\label{eq:REF:Reference Dimension, usually without tolerance, for information purposes only. \\$ 

Microchip Technology Drawing No. C04-057C Sheet 2 of 2

## 8-Lead Plastic Small Outline (SN) - Narrow, 3.90 mm Body [SOIC]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



RECOMMENDED LAND PATTERN

	Units	MILLIMETERS			
Dimension	Dimension Limits		NOM	MAX	
Contact Pitch	Е		1.27 BSC		
Contact Pad Spacing	С		5.40		
Contact Pad Width (X8)	X1			0.60	
Contact Pad Length (X8)	Y1			1.55	

#### Notes:

1. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing No. C04-2057A

NOTES:

## APPENDIX A: REVISION HISTORY

## Revision A (March 2011)

• Original Release of this Document.

# APPENDIX B: OFFSET RELATED TEST SCREENS

Input offset voltage related specifications in the DC spec table (Table 1-1) are based on bench measurements (see Section 2.1 "DC Input Precision"). These measurements are much more accurate because:

- · More compact circuit
- Soldered parts on the PCB (to validate other measurements)
- More time spent averaging (reduces noise)
- · Better temperature control
  - Reduced temperature gradients

- Greater accuracy

We use production screens to ensure the quality of our outgoing products. These screens are set at wider limits to eliminate any fliers; see Table B-1.

#### TABLE B-1: OFFSET RELATED TEST SCREENS

<b>Electrical Characteristics:</b> Unless otherwise indicated, $T_A = +25$ °C, $V_{DD} = +2.3$ V to +5.5V, $V_{SS} = GND$ ,							
$V_{CM} = V_{DD}/3$ , $V_{OUT} = V_{DD}/2$ , $V_L = V_{DD}/2$ and	$1d R_L = 1$	0 kΩ to	V <sub>L</sub> (re	fer to Fi	gure 1-4 and Figure 1-5).		
Parameters	Sym	Min	Max	Units	Conditions		
Input Offset							
Input Offset Voltage	Vos	-10	+10	μV	T <sub>A</sub> = +25°C (Note 1, Note 2)		
Input Offset Voltage Drift with Temperature (linear Temp. Co.)	TC <sub>1</sub>	_	_	nV/°C	$T_A = -40 \text{ to } +125^{\circ}\text{C (Note 3)}$		
Power Supply Rejection	PSRR	115	_	dB	(Note 1)		
Common Mode							
Common Mode Rejection	CMRR	106	_	dB	$V_{DD}$ = 2.3V, $V_{CM}$ = -0.15V to 2.5V (Note 1)		
	CMRR	116	_	dB	$V_{DD}$ = 5.5V, $V_{CM}$ = -0.15V to 5.7V (Note 1)		
Open-Loop Gain							
DC Open-Loop Gain (large signal)	A <sub>OL</sub>	114	_	dB	$V_{DD}$ = 2.3V, $V_{OUT}$ = 0.2V to 2.1V (Note 1)		
	A <sub>OL</sub>	122	_	dB	$V_{DD} = 5.5V$ , $V_{OUT} = 0.2V$ to 5.3V (Note 1)		

- **Note 1:** Due to thermal junctions and other errors in the production environment, these specifications are only screened in production.
  - 2: V<sub>OS</sub> is also sample screened at +125°C.
  - **3:**  $TC_1$  is not measured in production.

## PRODUCT IDENTIFICATION SYSTEM

To order or obtain information, e.g., on pricing or delivery, refer to the factory or the listed sales office.

PART NO.	<u>-X</u> / <u>XX</u>	Exa	amples:	
 Device Temp	 perature Package	a)	MCP6V27-E/MD:	Extended temperature, 8LD 4x4 DFN package
	MODOLVOZ	b)	MCP6V27T-E/MD:	Tape and Reel Extended temperature, 8LD 4x4 DFN package
Device:	MCP6V27 Dual Op Amp MCP6V27T Dual Op Amp (Tape and Reel)	c)	MCP6V27-E/MS:	Extended temperature, 8LD MSOP package
Temperature Range:	E = -40°C to +125°C	d)	MCP6V27T-E/MS:	Tape and Reel, Extended temperature, 8LD MSOP package.
Package:	MD = Plastic Dual Flat, No-Lead (4×4x0.9 mm), 8-lead MS = Plastic Micro Small Outline Package, 8-lead	e)	MCP6V27-E/SN:	Extended temperature, 8LD SOIC package.
	SN = Plastic SOIC (150 mil Body), 8-lead	f)	MCP6V27T-E/SN:	Tape and Reel, Extended temperature, 8LD SOIC package.

NOTES:

#### Note the following details of the code protection feature on Microchip devices:

- Microchip products meet the specification contained in their particular Microchip Data Sheet.
- Microchip believes that its family of products is one of the most secure families of its kind on the market today, when used in the intended manner and under normal conditions.
- There are dishonest and possibly illegal methods used to breach the code protection feature. All of these methods, to our
  knowledge, require using the Microchip products in a manner outside the operating specifications contained in Microchip's Data
  Sheets. Most likely, the person doing so is engaged in theft of intellectual property.
- · Microchip is willing to work with the customer who is concerned about the integrity of their code.
- Neither Microchip nor any other semiconductor manufacturer can guarantee the security of their code. Code protection does not mean that we are guaranteeing the product as "unbreakable."

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